

**AMENDMENTS TO THE CLAIMS**

The listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims**

Claims 1-5 (Cancelled)

6. (Currently Amended) A semiconductor integrated circuit, comprising:

a main circuit including a plurality of MOS transistors ~~of a MOS structure~~ in which a source potential and a substrate potential are separated from each other, and operating while receiving ~~a predetermined~~ an operating power supply voltage; and

a substrate potential control circuit for controlling the substrate potential of a MOS transistor in the main circuit so that ~~an actual~~ a saturation current value of the MOS transistor is equal to a target saturation current value, ~~that is sufficient to satisfy a desired operation speed of the main circuit given the operating power supply voltage value of the main circuit;~~ the substrate potential control circuit, including:

a constant current generation circuit;

a current-voltage conversion circuit including a MOS transistor provided therein and having current-voltage conversion characteristics that change according to the substrate potential of the MOS transistor provided therein for converting a constant current value of the constant current generation circuit to a voltage value; and

a differential amplifier circuit comparing the voltage value generated by the current-voltage conversion circuit with the operating power supply voltage and outputting a

voltage for controlling [[a]] the substrate potential of the current-voltage conversion circuit so that the voltage value generated by the current-voltage conversion circuit is equal to the predetermined operating power supply voltage value of the main circuit,

wherein the substrate potential control circuit controls [[the]] a substrate potential of each of the MOS transistors a MOS transistor in the main circuit ~~so that the substrate potential is equal to the substrate potential of the current-voltage conversion circuit controlled by the differential amplifier circuit.~~

7. (Currently Amended) The semiconductor integrated circuit of claim 6, wherein ~~where the predetermined operating power supply voltage of the main circuit varies within a predetermined operating voltage range, the constant current value of the constant current generation circuit is proportional to dependent on the operating power supply voltage value within the operating voltage range.~~

8. (Currently Amended) The semiconductor integrated circuit of claim 6, ~~wherein where the predetermined operating power supply voltage of the main circuit varies within a predetermined operating voltage range, the constant current value of the constant current generation circuit is in a linear function relationship with the operating power supply voltage value within the operating voltage range.~~

9. (Original) The semiconductor integrated circuit of claim 6, wherein:  
the main circuit has a plurality of operating power supply voltage ranges;

the constant current value of the constant current generation circuit is in a linear function relationship with an operating power supply voltage value within an operating voltage range for each operating power supply voltage range of the main circuit; and

the linear function relationship between the constant current value of the constant current generation circuit and the operating power supply voltage value is different for each operating power supply voltage range.

10. (Original) The semiconductor integrated circuit of claim 6, wherein the constant current generation circuit generates a plurality of constant current values, and selectively outputs one of the plurality of constant current values.

11. (Currently amended) The semiconductor integrated circuit of claim 6, wherein the constant current generation circuit generates a constant current with a variation rate smaller than that for the ~~actual~~ saturation current value of the MOS transistors of the main circuit.

12. (Original) The semiconductor integrated circuit of claim 11, wherein the constant current generation circuit includes an adjustment circuit for reducing variations in the generated constant current value.

Claims 13-14. (Cancelled)

15. (Currently Amended) ~~[[The]]~~ A semiconductor integrated circuit of claim 13, comprising:

a main circuit including a MOS transistor, and operating while receiving an operating power supply voltage; and

a power supply voltage control circuit for controlling the operating power supply voltage supplied to the main circuit, wherein:

a target saturation current value of the MOS transistors is set in the power supply voltage control circuit;

the power supply voltage control circuit controls a voltage value of the operating power supply voltage supplied to the main circuit so that an actual saturation current value of the MOS transistors of the main circuit is equal to the target saturation current value; and

the target saturation current value of the MOS transistors of the main circuit is in a linear function relationship with the operating power supply voltage supplied to the main circuit.

16. (Currently amended) [[The]] A semiconductor integrated circuit of claim 13, comprising:

a main circuit including a MOS transistor, and operating while receiving an operating power supply voltage; and

a power supply voltage control circuit for controlling the operating power supply voltage supplied to the main circuit, wherein:

a target saturation current value of the MOS transistors is set in the power supply voltage control circuit;

the power supply voltage control circuit controls a voltage value of the operating power supply voltage supplied to the main circuit so that an actual saturation current value of the MOS transistors of the main circuit is equal to the target saturation current value;

the main circuit includes a plurality of operating power supply voltage ranges;

the target saturation current value of the MOS transistors of the main circuit is in a linear function relationship with an operating power supply voltage value within an operating voltage range for each operating power supply voltage range of the main circuit; and

the linear function relationship between the target saturation current value and the operating power supply voltage value is different for each operating power supply voltage range.

17. (New) The semiconductor integrated circuit of claim 15, wherein the target saturation current value of the MOS transistors of the main circuit is a target saturation current value of an nMOS transistor or that of a pMOS transistor from among the MOS transistors of the main circuit, or is an average value between the target saturation current values of the nMOS and pMOS transistors.